



# UT2N06

## POWER MOSFET

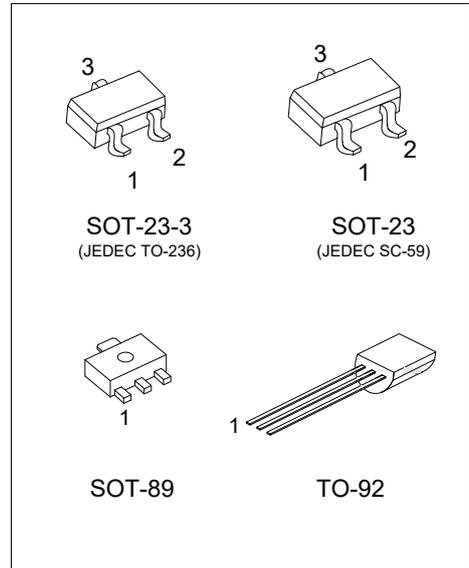
### 2.2A, 60V SHIELDED GATE N-CHANNEL POWER MOSFET

■ DESCRIPTION

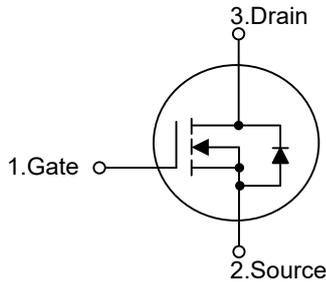
The UTC **UT2N06** is N-Channel MOSFET produced using advanced Power process that incorporates Shielded Gate technology. This process has been optimized for  $R_{DS(ON)}$ , switching performance and ruggedness.

■ FEATURES

- \*  $R_{DS(ON)} \leq 235 \text{ m}\Omega$  @  $V_{GS}=10\text{V}$ ,  $I_D=2.2\text{A}$
- $R_{DS(ON)} \leq 280 \text{ m}\Omega$  @  $V_{GS}=4.5\text{V}$ ,  $I_D=1.3\text{A}$
- \* Simple drive requirement
- \* Small package outline
- \* Fast Switching Speed



■ SYMBOL



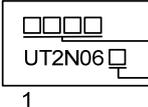
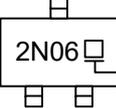
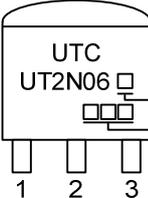
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UT2N06L-AB3-R	UT2N06G-AB3-R	SOT-89	G	D	S	Tape Reel
UT2N06L-AE2-R	UT2N06G-AE2-R	SOT-23-3	G	S	D	Tape Reel
UT2N06L-AE3-R	UT2N06G-AE3-R	SOT-23	G	S	D	Tape Reel
UT2N06L-T92-B	UT2N06G-T92-B	TO-92	S	G	D	Tape Box
UT2N06L-T92-K	UT2N06G-T92-K	TO-92	S	G	D	Bulk

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>UT2N06G-AB3-R</p>	<p>(1) Packing Type</p> <p>(2) Package Type</p> <p>(3) Green Package</p>	<p>(1) R: Tape Reel, B: Tape Box, K: Bulk</p> <p>(2) AB3: SOT-89, AE2: SOT-23-3, AE3: SOT-23</p> <p>T92: TO-92</p> <p>(3) G: Halogen Free and Lead Free, L: Lead Free</p>
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■ MARKING

PACKAGE	MARKING
SOT-89	 <p>                     Date Code                      L: Lead Free                      G: Halogen Free                 </p>
SOT-23-3 / SOT-23	 <p>                     L: Lead Free                      G: Halogen Free                 </p>
TO-92	 <p>                     L: Lead Free                      G: Halogen Free                      Date Code                 </p>

■ ABSOLUTE MAXIMUM RATING ( $T_A=25^{\circ}\text{C}$ , unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		$V_{DSS}$	60	V
Gate-Source Voltage		$V_{GSS}$	$\pm 20$	V
Drain Current	Continuous	$I_D$	2.2	A
	Pulsed	$I_{DM}$	6.6	A
Avalanche Energy	Single Pulsed (Note 4)	$E_{AS}$	245	mJ
Peak Diode Recovery dv/dt (Note 5)		dv/dt	0.896	V/ns
Power Dissipation (Note 3)	SOT-23-3	$P_D$	400	mW
	SOT-23		500	mW
	SOT-89		1000	mW
	TO-92		625	mW
Junction Temperature		$T_J$	+150	$^{\circ}\text{C}$
Storage Temperature Range		$T_{STG}$	-55 ~ +150	$^{\circ}\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. Surface mounted on 1 in<sup>2</sup> copper pad of FR-4 board. 270 $^{\circ}\text{C}/\text{W}$  when mounted on minimum copper pad.

4.  $L=10\text{mH}$ ,  $I_{AS}=7.0\text{A}$ ,  $V_{DD}=20\text{V}$ ,  $R_G=25\ \Omega$ , Starting  $T_J = 25^{\circ}\text{C}$

5.  $I_{SD}\leq 3.0\text{A}$ ,  $di/dt\leq 200\text{A}/\mu\text{s}$ ,  $V_{DD}\leq BV_{DSS}$ , Starting  $T_J = 25^{\circ}\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	SOT-23-3	$\theta_{JA}$	312	$^{\circ}\text{C}/\text{W}$
	SOT-23		250	$^{\circ}\text{C}/\text{W}$
	SOT-89		125	$^{\circ}\text{C}/\text{W}$
	TO-92		200	$^{\circ}\text{C}/\text{W}$

Note: Surface mounted on 1 in<sup>2</sup> copper pad of FR-4 board. 270 $^{\circ}\text{C}/\text{W}$  when mounted on minimum copper pad.

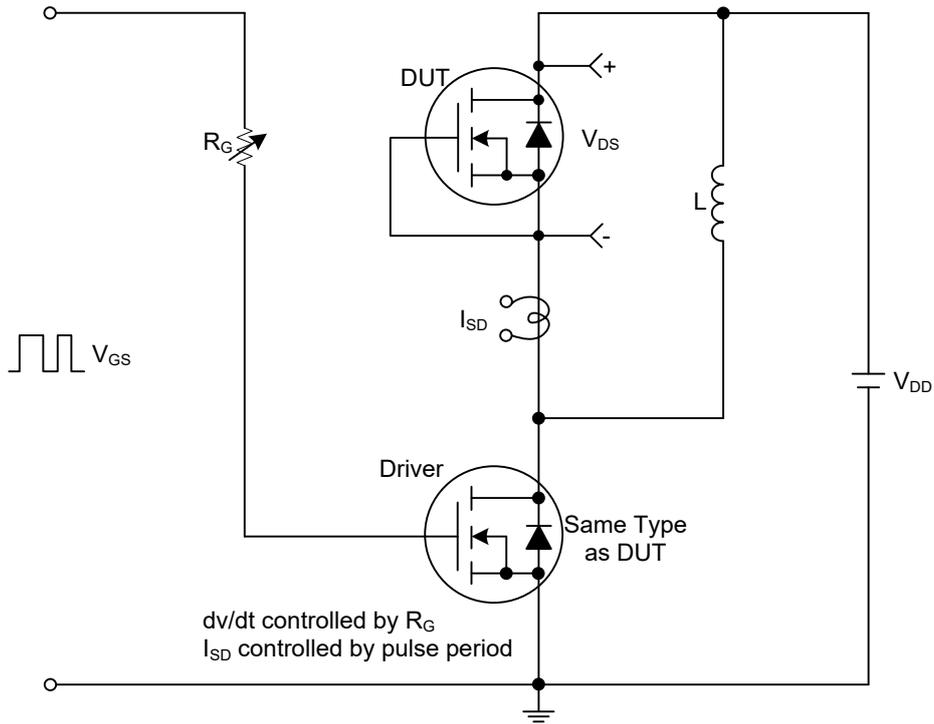
■ ELECTRICAL CHARACTERISTICS (T<sub>J</sub>=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	60			V
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V			1	μA
Gate-Source Leakage Current	Forward	V <sub>GS</sub> =+20V, V <sub>DS</sub> =0V V <sub>GS</sub> =-20V, V <sub>DS</sub> =0V			+100	nA
	Reverse				-100	nA
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.0		2.5	V
Static Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =2.2A			235	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =1.3A			280	mΩ
<b>DYNAMIC PARAMETERS</b>						
Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =30V, f=1.0MHz		112		pF
Output Capacitance	C <sub>OSS</sub>			21		pF
Reverse Transfer Capacitance	C <sub>RSS</sub>			14		pF
<b>SWITCHING PARAMETERS</b>						
Total Gate Charge (Note 1)	Q <sub>G</sub>	V <sub>DS</sub> =48V, V <sub>GS</sub> =10V, I <sub>D</sub> =2.2A I <sub>G</sub> =1mA (Note 1, 2)		7.1		nC
Gate to Source Charge	Q <sub>GS</sub>			1.0		nC
Gate to Drain Charge	Q <sub>GD</sub>			1.6		nC
Turn-on Delay Time (Note 1)	t <sub>D(ON)</sub>	V <sub>DD</sub> =30V, V <sub>GS</sub> =10V, I <sub>D</sub> =3.0A, R <sub>G</sub> =25Ω (Note 1, 2)		4.0		ns
Rise Time	t <sub>R</sub>			15		ns
Turn-off Delay Time	t <sub>D(OFF)</sub>			50		ns
Fall-Time	t <sub>F</sub>			25		ns
<b>SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS</b>						
Maximum Body-Diode Continuous Current	I <sub>S</sub>				2.2	A
Maximum Body-Diode Pulsed Current	I <sub>SM</sub>				6.6	A
Drain-Source Diode Forward Voltage (Note 1)	V <sub>SD</sub>	I <sub>S</sub> =0.45A, V <sub>GS</sub> =0V			1.0	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>S</sub> =1.0A, V <sub>GS</sub> =0V,		62.8		ns
Reverse Recovery Charge	Q <sub>rr</sub>	dI <sub>F</sub> /dI <sub>t</sub> =100A/μs		0.34		μC

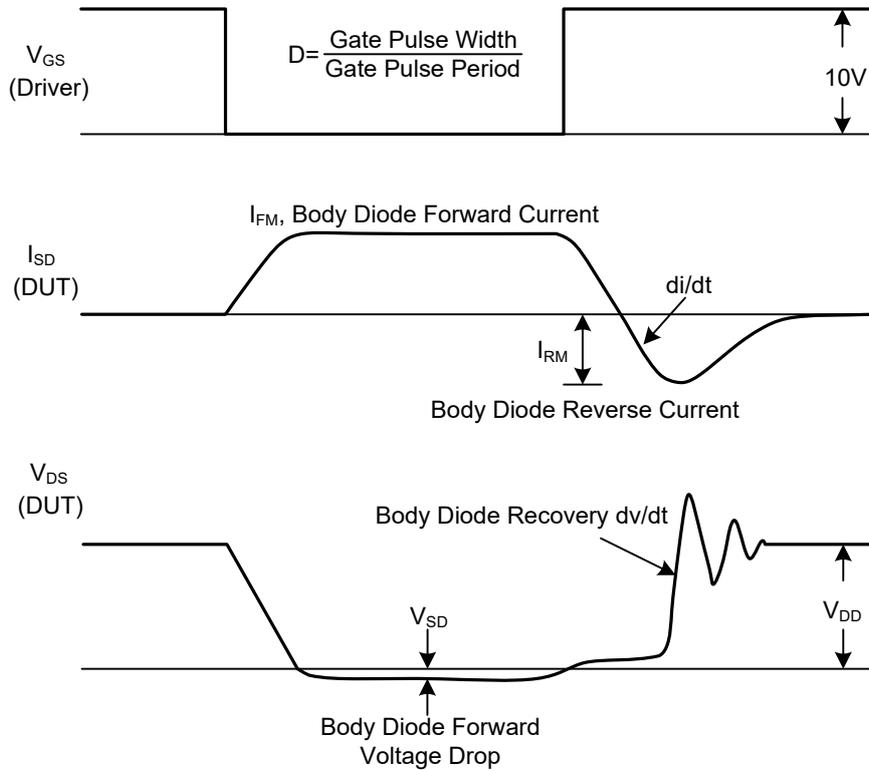
Notes: 1. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%.

2. Essentially independent of operating temperature.

TEST CIRCUITS AND WAVEFORMS



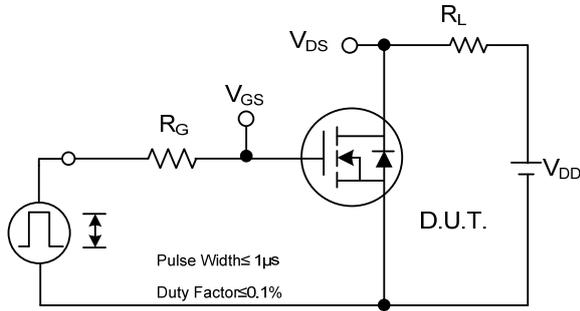
Peak Diode Recovery dv/dt Test Circuit



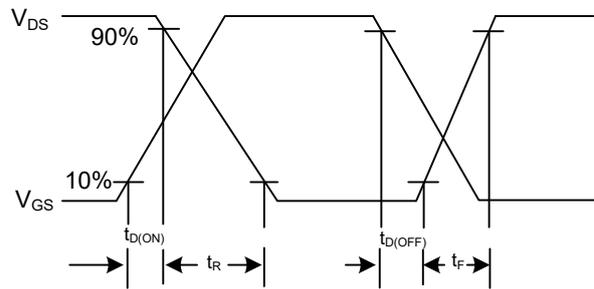
Peak Diode Recovery dv/dt Test Circuit and Waveforms

Peak Diode Recovery dv/dt Waveforms

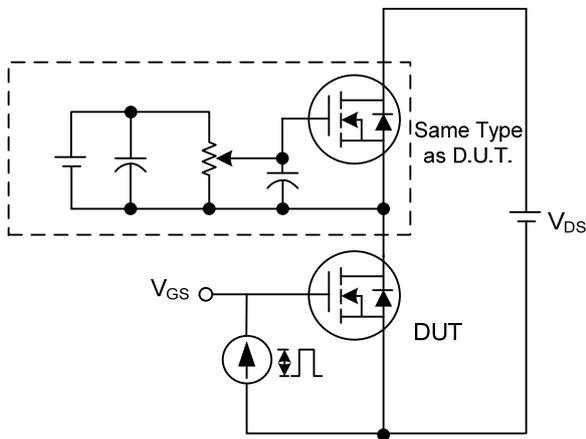
■ TEST CIRCUITS AND WAVEFORMS



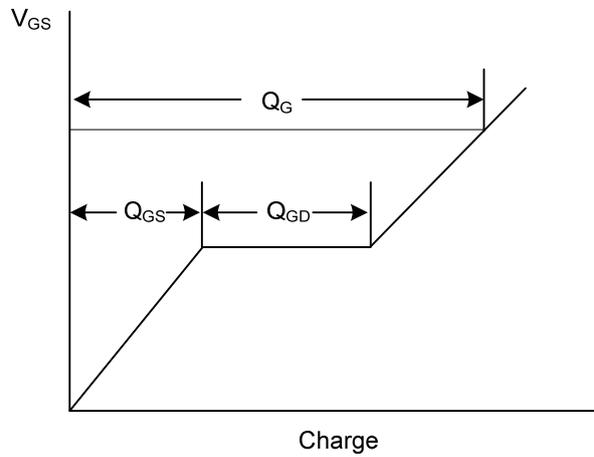
Switching Test Circuit



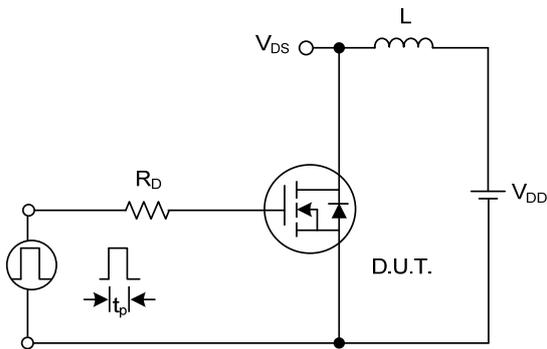
Switching Waveforms



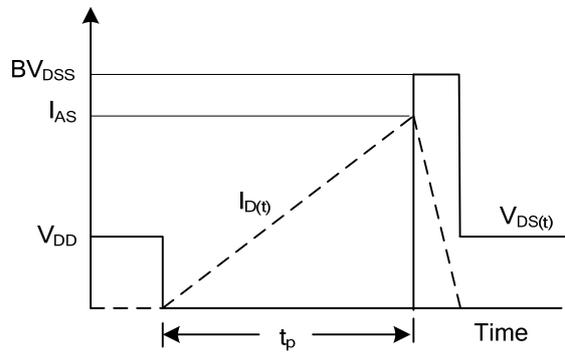
Gate Charge Test Circuit



Gate Charge Waveform

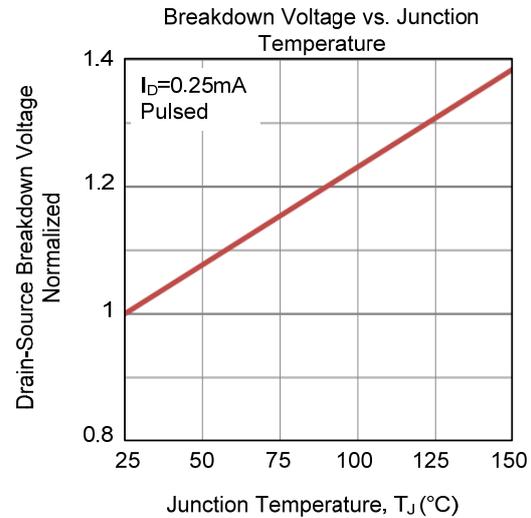
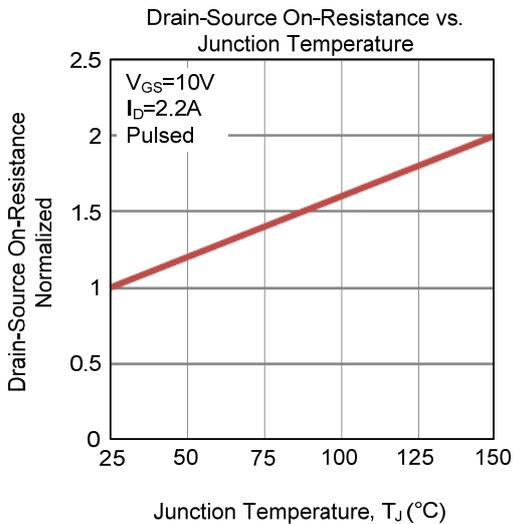
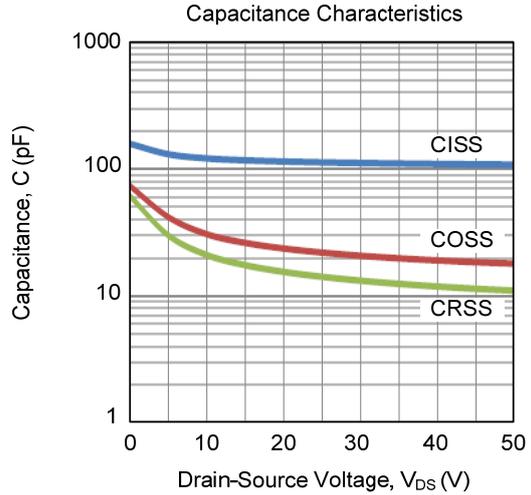
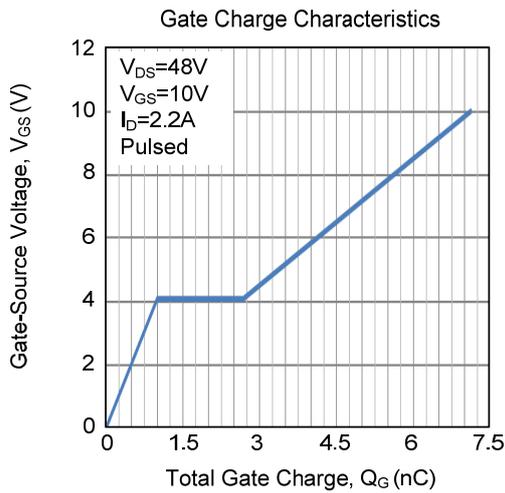
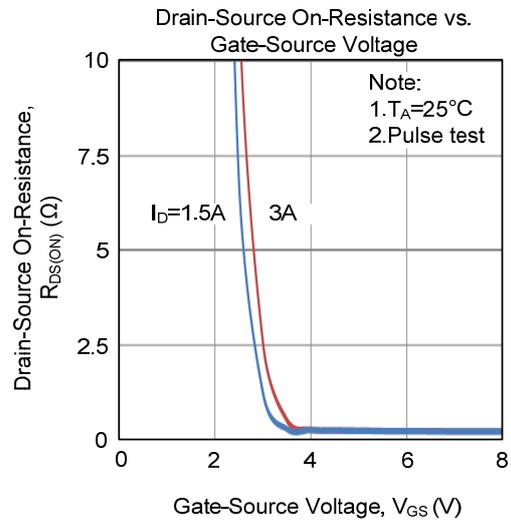
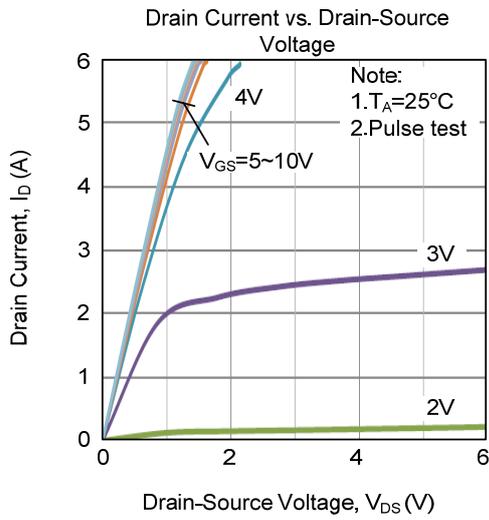


Unclamped Inductive Switching Test Circuit

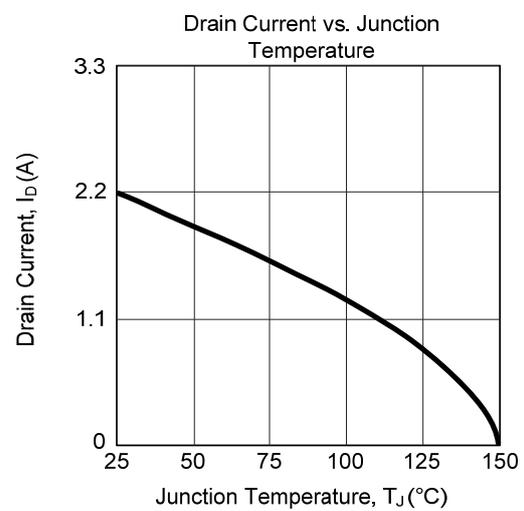
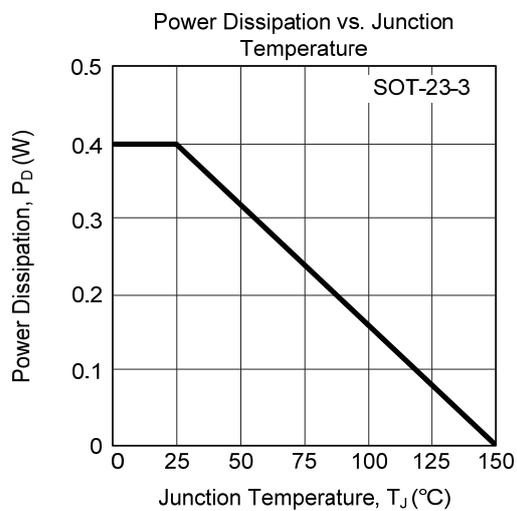
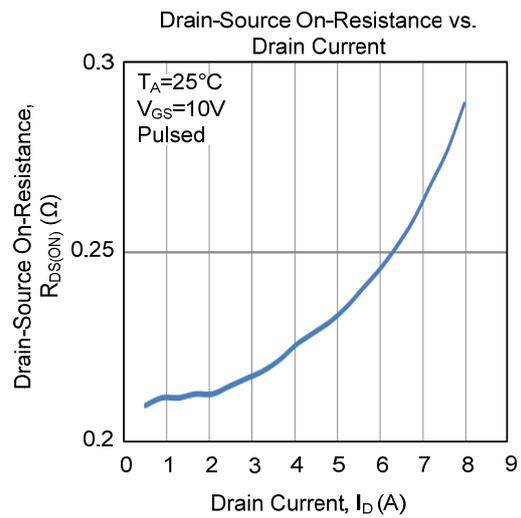
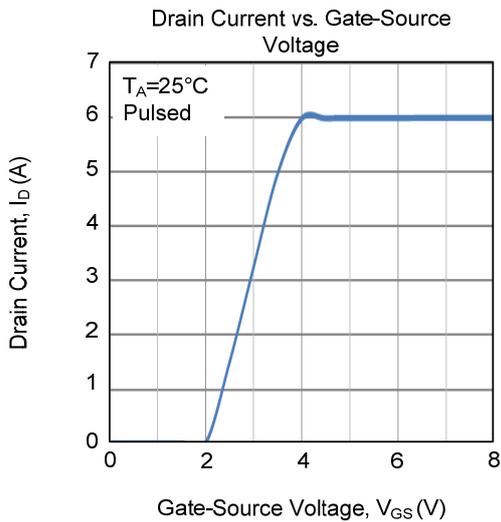
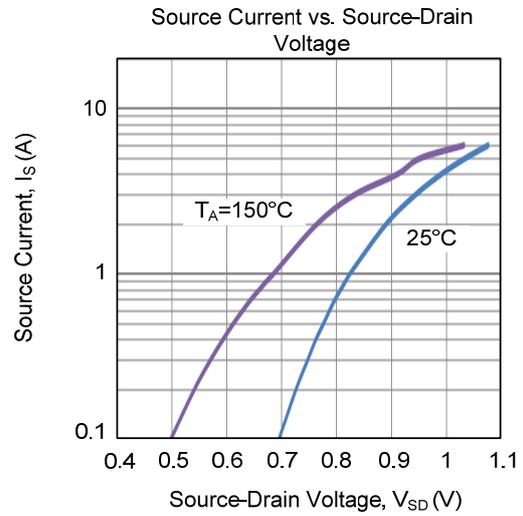
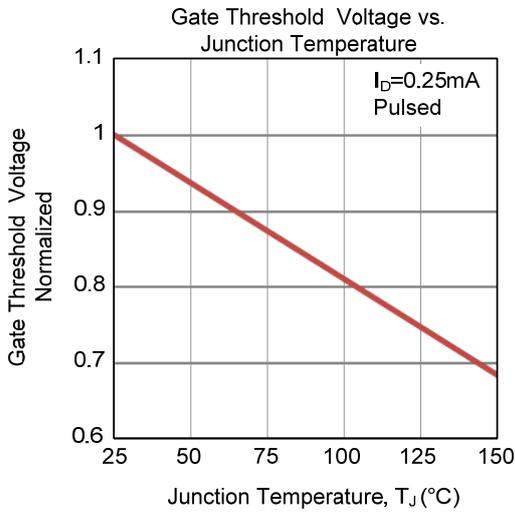


Unclamped Inductive Switching Waveforms

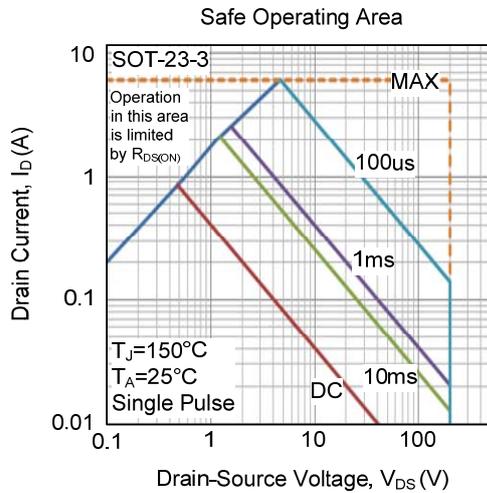
## TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



■ TYPICAL CHARACTERISTICS (Cont.)



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